



N-Channel 60-V (D-S) Fast Switching MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ.)		
60	0.0083 at $V_{GS} = 10 \text{ V}$	19.3	105		

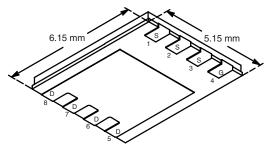
FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET[®] Power MOSFET
- New Low Thermal Resistance PowerPAK[®]
 Package with Low 1.07 mm Profile
- 100 % R_g Tested
- High Threshold Voltage At High Temperature





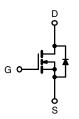
PowerPAK SO-8



Bottom View

Ordering Information: Si7452DP-T1-E3 (Lead (Pb)-free)

Si7452DP-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V_{DS}	60		V
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current (T, = 150 °C) ^a	T _A = 25 °C	I _D	19.3	11.5	
Continuous Diain Current (1) = 150 °C)	T _A = 70 °C		15.5	9.2	
Pulsed Drain Current		I _{DM}	60		Α
Continuous Source Current (Diode Conduction) ^a		I _S	4.5	1.6	
Avalanche Current		I _{AS}	40		
Avalanche Energy		E _{AS}	80		mJ
Mariana Dama Dissipationa	T _A = 25 °C	P _D	5.4	1.9	W
Maximum Power Dissipation ^a	T _A = 70 °C		3.4	1.2	VV
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C
Soldering Recommendations (Peak Temperature) ^{b,c}			260		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	t ≤ 10 s	R _{thJA}	18	23	°C/W	
Maximum Junction-to-Ambient	Steady State		52	65		
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	1.0	1.3		

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. See Solder Profile (<u>www.vishay.com/ppg?73257</u>). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

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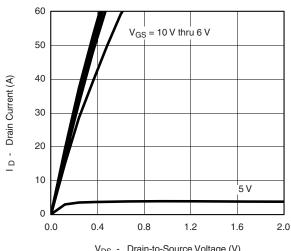
MOSFET SPECIFICATIONS T _J = 25 °C, unless otherwise noted									
Parameter	Symbol	Test Condition	Min.	Тур.	Max.	Unit			
Static									
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	3.4		4.5	V			
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA			
Zava Cata Valta va Duais Occurat	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V			1				
Zero Gate Voltage Drain Current		$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			5	μΑ			
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	40			Α			
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 19.3 A		0.007	0.0083	Ω			
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 19.3 A		51		S			
Diode Forward Voltage ^a	V_{SD}	$I_S = 4.5 \text{ A}, V_{GS} = 0 \text{ V}$		0.8	1.2	V			
Dynamic ^b									
Total Gate Charge	Q_g			105	160	nC			
Gate-Source Charge	Q _{gs}	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 19.3 \text{ A}$		40					
Gate-Drain Charge	Q_{gd}			21					
Gate Resistance	R_g	f = 1 MHz	0.5	1.0	1.5	Ω			
Turn-On Delay Time	t _{d(on)}			45	70				
Rise Time	t _r	V_{DD} = 30 V, R_L = 30 Ω		15	25	ns			
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ 1 A, V_{GEN} = 10 V, R_g = 6 Ω		90	135				
Fall Time	t _f			40	60				
Source-Drain Reverse Recovery Time	t _{rr}	$I_F = 4.5 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}$		46	70				

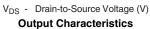
Notes:

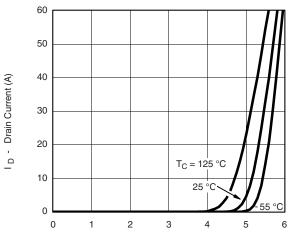
- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted







V_{GS} - Gate-to-Source Voltage (V)

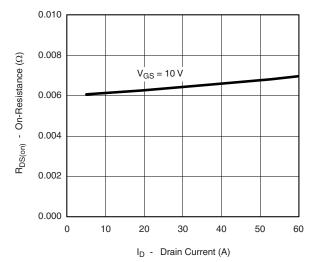
Transfer Characteristics



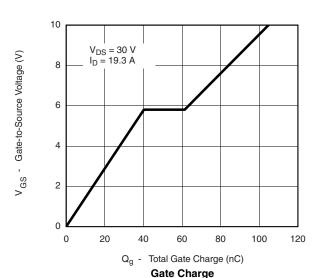


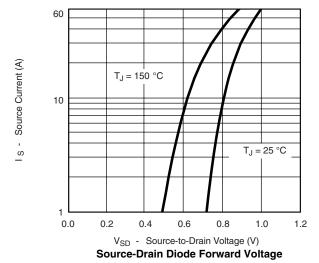


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



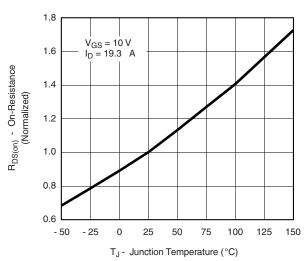
On-Resistance vs. Drain Current



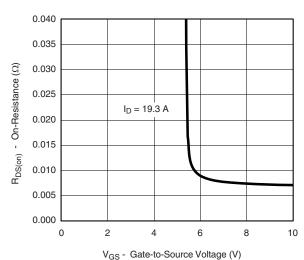


10000 8000 Ciss C - Capacitance (pF) 6000 4000 2000 Coss 0 20 30 0 10 40 50 60

V_{DS} - Drain-to-Source Voltage (V) **Capacitance**



On-Resistance vs. Junction Temperature

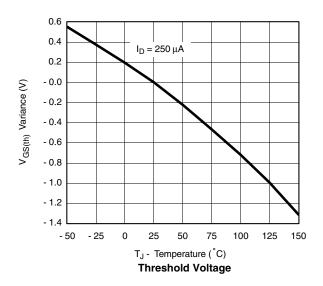


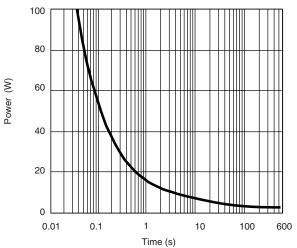
On-Resistance vs. Gate-to-Source Voltage

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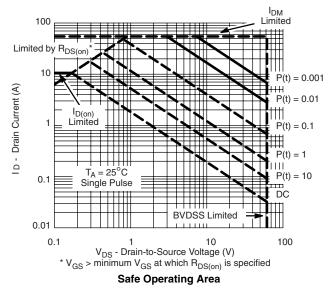
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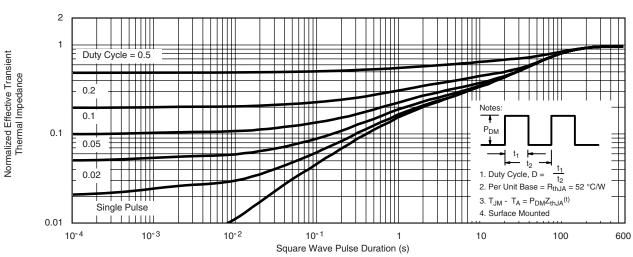
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





Single Pulse Power, Junction-to-Ambient

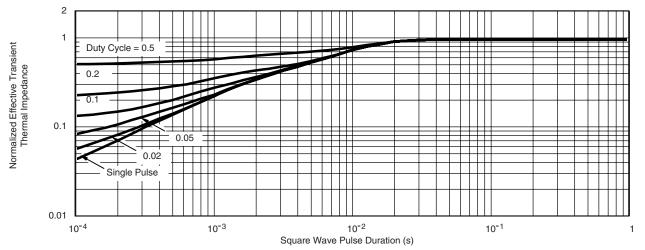




Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Case

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